

ABSTRACT OF THE DISCLOSURE

The present invention teaches an apparatus for pulling a single crystal, whereby the radial temperature gradient of a seed crystal and/or a neck is reduced to a minimum so as to inhibit the occurrence of thermal stress and prevent induction of dislocations, resulting in an improvement in dislocation-free rate of single crystals to be pulled in cases where a single crystal is pulled with the seed crystal and/or the neck being heated using an auxiliary heating device, comprising a crucible charged with a melt, a heater located around the crucible and an auxiliary heating device including a heating section which can be located so as to surround a seed crystal in a position near above the melt and a transfer mechanism for withdrawing the heating section from a passing area of a single crystal, wherein a covering section to cover a clearance between the heating section and the seed crystal is extended from the heating section.